E. Lattice Semiconductor Corporation - <u>LFE3-95EA-8LFN672C Datasheet</u>



Welcome to E-XFL.COM

Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	11500
Number of Logic Elements/Cells	92000
Total RAM Bits	4526080
Number of I/O	380
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	672-BBGA
Supplier Device Package	672-FPBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe3-95ea-8lfn672c

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



The edge clocks on the top, left, and right sides of the device can drive the secondary clocks or general routing resources of the device. The left and right side edge clocks also can drive the primary clock network through the clock dividers (CLKDIV).

sysMEM Memory

LatticeECP3 devices contain a number of sysMEM Embedded Block RAM (EBR). The EBR consists of an 18-Kbit RAM with memory core, dedicated input registers and output registers with separate clock and clock enable. Each EBR includes functionality to support true dual-port, pseudo dual-port, single-port RAM, ROM and FIFO buffers (via external PFUs).

sysMEM Memory Block

The sysMEM block can implement single port, dual port or pseudo dual port memories. Each block can be used in a variety of depths and widths as shown in Table 2-7. FIFOs can be implemented in sysMEM EBR blocks by implementing support logic with PFUs. The EBR block facilitates parity checking by supporting an optional parity bit for each data byte. EBR blocks provide byte-enable support for configurations with18-bit and 36-bit data widths. For more information, please see TN1179, LatticeECP3 Memory Usage Guide.

Table 2-7. sysMEM Block Configurations

Memory Mode	Configurations
Single Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18 512 x 36
True Dual Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18
Pseudo Dual Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18 512 x 36

Bus Size Matching

All of the multi-port memory modes support different widths on each of the ports. The RAM bits are mapped LSB word 0 to MSB word 0, LSB word 1 to MSB word 1, and so on. Although the word size and number of words for each port varies, this mapping scheme applies to each port.

RAM Initialization and ROM Operation

If desired, the contents of the RAM can be pre-loaded during device configuration. By preloading the RAM block during the chip configuration cycle and disabling the write controls, the sysMEM block can also be utilized as a ROM.

Memory Cascading

Larger and deeper blocks of RAM can be created using EBR sysMEM Blocks. Typically, the Lattice design tools cascade memory transparently, based on specific design inputs.







Note: Simplified diagram does not show CE/SET/REST details.

Output Register Block

The output register block registers signals from the core of the device before they are passed to the sysl/O buffers. The blocks on the left and right PIOs contain registers for SDR and full DDR operation. The topside PIO block is the same as the left and right sides except it does not support ODDRX2 gearing of output logic. ODDRX2 gearing is used in DDR3 memory interfaces. The PIO blocks on the bottom contain the SDR registers but do not support generic DDR.

Figure 2-34 shows the Output Register Block for PIOs on the left and right edges.

In SDR mode, OPOSA feeds one of the flip-flops that then feeds the output. The flip-flop can be configured as a Dtype or latch. In DDR mode, two of the inputs are fed into registers on the positive edge of the clock. At the next clock cycle, one of the registered outputs is also latched.

A multiplexer running off the same clock is used to switch the mux between the 11 and 01 inputs that will then feed the output.

A gearbox function can be implemented in the output register block that takes four data streams: OPOSA, ONEGA, OPOSB and ONEGB. All four data inputs are registered on the positive edge of the system clock and two of them are also latched. The data is then output at a high rate using a multiplexer that runs off the DQCLK0 and DQCLK1 clocks. DQCLK0 and DQCLK1 are used in this case to transfer data from the system clock to the edge clock domain. These signals are generated in the DQS Write Control Logic block. See Figure 2-37 for an overview of the DQS write control logic.

Please see TN1180, LatticeECP3 High-Speed I/O Interface for more information on this topic.

Further discussion on using the DQS strobe in this module is discussed in the DDR Memory section of this data sheet.



DLL Calibrated DQS Delay Block

Source synchronous interfaces generally require the input clock to be adjusted in order to correctly capture data at the input register. For most interfaces, a PLL is used for this adjustment. However, in DDR memories the clock (referred to as DQS) is not free-running so this approach cannot be used. The DQS Delay block provides the required clock alignment for DDR memory interfaces.

The delay required for the DQS signal is generated by two dedicated DLLs (DDR DLL) on opposite side of the device. Each DLL creates DQS delays in its half of the device as shown in Figure 2-36. The DDR DLL on the left side will generate delays for all the DQS Strobe pins on Banks 0, 7 and 6 and DDR DLL on the right will generate delays for all the DQS pins on Banks 1, 2 and 3. The DDR DLL loop compensates for temperature, voltage and process variations by using the system clock and DLL feedback loop. DDR DLL communicates the required delay to the DQS delay block using a 7-bit calibration bus (DCNTL[6:0])

The DQS signal (selected PIOs only, as shown in Figure 2-35) feeds from the PAD through a DQS control logic block to a dedicated DQS routing resource. The DQS control logic block consists of DQS Read Control logic block that generates control signals for the read side and DQS Write Control logic that generates the control signals required for the write side. A more detailed DQS control diagram is shown in Figure 2-37, which shows how the DQS control blocks interact with the data paths.

The DQS Read control logic receives the delay generated by the DDR DLL on its side and delays the incoming DQS signal by 90 degrees. This delayed ECLKDQSR is routed to 10 or 11 DQ pads covered by that DQS signal. This block also contains a polarity control logic that generates a DDRCLKPOL signal, which controls the polarity of the clock to the sync registers in the input register blocks. The DQS Read control logic also generates a DDRLAT signal that is in the input register block to transfer data from the first set of DDR register to the second set of DDR registers when using the DDRX2 gearbox mode for DDR3 memory interface.

The DQS Write control logic block generates the DQCLK0 and DQCLK1 clocks used to control the output gearing in the Output register block which generates the DDR data output and the DQS output. They are also used to control the generation of the DQS output through the DQS output register block. In addition to the DCNTL [6:0] input from the DDR DLL, the DQS Write control block also uses a Dynamic Delay DYN DEL [7:0] attribute which is used to further delay the DQS to accomplish the write leveling found in DDR3 memory. Write leveling is controlled by the DDR memory controller implementation. The DYN DELAY can set 128 possible delay step settings. In addition, the most significant bit will invert the clock for a 180-degree shift of the incoming clock. This will generate the DQSW signal used to generate the DQS output in the DQS output register block.

Figure 2-36 and Figure 2-37 show how the DQS transition signals that are routed to the PIOs.

Please see TN1180, LatticeECP3 High-Speed I/O Interface for more information on this topic.



Please see TN1177, LatticeECP3 sysIO Usage Guide for on-chip termination usage and value ranges.

Equalization Filter

Equalization filtering is available for single-ended inputs on both true and complementary I/Os, and for differential inputs on the true I/Os on the left, right, and top sides. Equalization is required to compensate for the difficulty of sampling alternating logic transitions with a relatively slow slew rate. It is considered the most useful for the Input DDRX2 modes, used in DDR3 memory, LVDS, or TRLVDS signaling. Equalization filter acts as a tunable filter with settings to determine the level of correction. In the LatticeECP3 devices, there are four settings available: 0 (none), 1, 2 and 3. The default setting is 0. The equalization logic resides in the sysI/O buffers, the two bits of setting is set uniquely in each input IOLOGIC block. Therefore, each sysI/O can have a unique equalization setting within a DQS-12 group.

Hot Socketing

LatticeECP3 devices have been carefully designed to ensure predictable behavior during power-up and powerdown. During power-up and power-down sequences, the I/Os remain in tri-state until the power supply voltage is high enough to ensure reliable operation. In addition, leakage into I/O pins is controlled within specified limits. Please refer to the Hot Socketing Specifications in the DC and Switching Characteristics in this data sheet.

SERDES and PCS (Physical Coding Sublayer)

LatticeECP3 devices feature up to 16 channels of embedded SERDES/PCS arranged in quads at the bottom of the devices supporting up to 3.2Gbps data rate. Figure 2-40 shows the position of the quad blocks for the LatticeECP3-150 devices. Table 2-14 shows the location of available SERDES Quads for all devices.

The LatticeECP3 SERDES/PCS supports a range of popular serial protocols, including:

- PCI Express 1.1
- Ethernet (XAUI, GbE 1000 Base CS/SX/LX and SGMII)
- Serial RapidIO
- SMPTE SDI (3G, HD, SD)
- CPRI
- SONET/SDH (STS-3, STS-12, STS-48)

Each quad contains four dedicated SERDES for high speed, full duplex serial data transfer. Each quad also has a PCS block that interfaces to the SERDES channels and contains protocol specific digital logic to support the standards listed above. The PCS block also contains interface logic to the FPGA fabric. All PCS logic for dedicated protocol support can also be bypassed to allow raw 8-bit or 10-bit interfaces to the FPGA fabric.

Even though the SERDES/PCS blocks are arranged in quads, multiple baud rates can be supported within a quad with the use of dedicated, per channel \div 1, \div 2 and \div 11 rate dividers. Additionally, multiple quads can be arranged together to form larger data pipes.

For information on how to use the SERDES/PCS blocks to support specific protocols, as well on how to combine multiple protocols and baud rates within a device, please refer to TN1176, LatticeECP3 SERDES/PCS Usage Guide.



Figure 2-40. SERDES/PCS Quads (LatticeECP3-150)



Table 2-13. LatticeECP3 SERDES Standard Support

Standard	Data Rate (Mbps)	Number of General/Link Width	Encoding Style
PCI Express 1.1	2500	x1, x2, x4	8b10b
Gigabit Ethernet	1250, 2500	x1	8b10b
SGMII	1250	x1	8b10b
XAUI	3125	x4	8b10b
Serial RapidIO Type I, Serial RapidIO Type II, Serial RapidIO Type III	1250, 2500, 3125	x1, x4	8b10b
CPRI-1, CPRI-2, CPRI-3, CPRI-4	614.4, 1228.8, 2457.6, 3072.0	x1	8b10b
SD-SDI (259M, 344M)	143 ¹ , 177 ¹ , 270, 360, 540	x1	NRZI/Scrambled
HD-SDI (292M)	1483.5, 1485	x1	NRZI/Scrambled
3G-SDI (424M)	2967, 2970	x1	NRZI/Scrambled
SONET-STS-3 ²	155.52	x1	N/A
SONET-STS-12 ²	622.08	x1	N/A
SONET-STS-48 ²	2488	x1	N/A

1. For slower rates, the SERDES are bypassed and CML signals are directly connected to the FPGA routing.

2. The SONET protocol is supported in 8-bit SERDES mode. See TN1176 Lattice ECP3 SERDES/PCS Usage Guide for more information.



LatticeECP3 Supply Current (Standby)^{1, 2, 3, 4, 5, 6}

			Тур	Typical	
Symbol	Parameter	Device	-6L, -7L, -8L	-6, -7, -8	Units
		ECP-17EA	29.8	49.4	mA
		ECP3-35EA	53.7	89.4	mA
I _{CC}	Core Power Supply Current	ECP3-70EA	137.3	230.7	mA
		ECP3-95EA	137.3	230.7	mA
		ECP3-150EA	219.5	370.9	mA
		ECP-17EA	18.3	19.4	mA
		ECP3-35EA	19.6	23.1	mA
I _{CCAUX}	Auxiliary Power Supply Current	ECP3-70EA	26.5	32.4	mA
		ECP3-95EA	26.5	32.4	mA
		ECP3-150EA	37.0	45.7	mA
		ECP-17EA	0.0	0.0	mA
	PLL Power Supply Current (Per PLL)	ECP3-35EA	0.1	0.1	mA
		ECP3-70EA	0.1	0.1	mA
		ECP3-95EA	0.1	0.1	mA
		ECP3-150EA	0.1	0.1	mA
		ECP-17EA	1.3	1.4	mA
		ECP3-35EA	1.3	1.4	mA
I _{CCIO}	Bank Power Supply Current (Per Bank)	ECP3-70EA	1.4	1.5	mA
		ECP3-95EA	1.4	1.5	mA
		ECP3-150EA	1.4	1.5	mA
I _{CCJ}	JTAG Power Supply Current	All Devices	2.5	2.5	mA
		ECP-17EA	6.1	6.1	mA
		ECP3-35EA	6.1	6.1	mA
I _{CCA}	Iransmit, Receive, PLL and Reference Clock Buffer Power Supply	ECP3-70EA	18.3	18.3	mA
		ECP3-95EA	18.3	18.3	mA
		ECP3-150EA	24.4	24.4	mA

Over Recommended Operating Conditions

1. For further information on supply current, please see the list of technical documentation at the end of this data sheet.

2. Assumes all outputs are tristated, all inputs are configured as LVCMOS and held at the $V_{\mbox{CCIO}}$ or GND.

3. Frequency 0 MHz.

4. Pattern represents a "blank" configuration data file.

5. $T_J = 85$ °C, power supplies at nominal voltage.

6. To determine the LatticeECP3 peak start-up current data, use the Power Calculator tool.



Units V

Ω

Ω

Ω

Ω

٧

٧

V

V

mΑ

BLVDS25

The LatticeECP3 devices support the BLVDS standard. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel external resistor across the driver outputs. BLVDS is intended for use when multi-drop and bi-directional multi-point differential signaling is required. The scheme shown in Figure 3-2 is one possible solution for bi-directional multi-point differential signals.





Table 3-2. BLVDS25 DC Conditions¹

V_{CCIO}

ZOUT

R_S

R_{TL}

 R_{TR} V_{OH}

VOL

VOD

V_{CM}

	-	-		
		Typical		
Parameter	Description	Ζο = 45 Ω	Ζο = 90 Ω	
CCIO	Output Driver Supply (+/– 5%)	2.50	2.50	

10.00

90.00

45.00

45.00

1.38

1.12

0.25

1.25

11.24

10.00

90.00

90.00

90.00

1.48

1.02

0.46

1.25

10.20

Over Recommended Operating Conditions

 I_{DC} 1. For input buffer, see LVDS table.

Driver Impedance

Output High Voltage

Output Low Voltage

DC Output Current

Output Differential Voltage

Output Common Mode Voltage

Driver Series Resistor (+/- 1%)

Driver Parallel Resistor (+/- 1%)

Receiver Termination (+/- 1%)



Typical Building Block Function Performance

Pin-to-Pin Performance (LVCMOS25 12 mA Drive)^{1, 2, 3}

Function	–8 Timing	Units
Basic Functions		
16-bit Decoder	4.7	ns
32-bit Decoder	4.7	ns
64-bit Decoder	5.7	ns
4:1 MUX	4.1	ns
8:1 MUX	4.3	ns
16:1 MUX	4.7	ns
32:1 MUX	4.8	ns

1. These functions were generated using the ispLEVER design tool. Exact performance may vary with device and tool version. The tool uses internal parameters that have been characterized but are not tested on every device.

2. Commercial timing numbers are shown. Industrial numbers are typically slower and can be extracted from the Diamond or ispLEVER software.

Register-to-Register Performance^{1, 2, 3}

Function	–8 Timing	Units
Basic Functions		
16-bit Decoder	500	MHz
32-bit Decoder	500	MHz
64-bit Decoder	500	MHz
4:1 MUX	500	MHz
8:1 MUX	500	MHz
16:1 MUX	500	MHz
32:1 MUX	445	MHz
8-bit adder	500	MHz
16-bit adder	500	MHz
64-bit adder	305	MHz
16-bit counter	500	MHz
32-bit counter	460	MHz
64-bit counter	320	MHz
64-bit accumulator	315	MHz
Embedded Memory Functions		
512x36 Single Port RAM, EBR Output Registers	340	MHz
1024x18 True-Dual Port RAM (Write Through or Normal, EBR Output Registers)	340	MHz
1024x18 True-Dual Port RAM (Read-Before-Write, EBR Output Registers	130	MHz
1024x18 True-Dual Port RAM (Write Through or Normal, PLC Output Registers)	245	MHz
Distributed Memory Functions		
16x4 Pseudo-Dual Port RAM (One PFU)	500	MHz
32x4 Pseudo-Dual Port RAM	500	MHz
64x8 Pseudo-Dual Port RAM	400	MHz
DSP Function		
18x18 Multiplier (All Registers)	400	MHz
9x9 Multiplier (All Registers)	400	MHz
36x36 Multiply (All Registers)	260	MHz



LatticeECP3 External Switching Characteristics (Continued)^{1, 2, 3, 13}

			-	-8	-	-7	-	-6	
Parameter	Description	Device	Min.	Max.	Min.	Max.	Min.	Max.	Units
t _{H_DEL}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-150EA	0.0	_	0.0	—	0.0	—	ns
f _{MAX_IO}	Clock Frequency of I/O and PFU Register	ECP3-150EA		500		420		375	MHz
t _{CO}	Clock to Output - PIO Output Register	ECP3-70EA/95EA	—	3.8	—	4.2	_	4.6	ns
t _{SU}	Clock to Data Setup - PIO Input Register	ECP3-70EA/95EA	0.0	—	0.0	_	0.0	—	ns
t _H	Clock to Data Hold - PIO Input Register	ECP3-70EA/95EA	1.4	—	1.6	—	1.8	—	ns
t _{SU_DEL}	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-70EA/95EA	1.3	—	1.5	—	1.7	—	ns
t _{H_DEL}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-70EA/95EA	0.0	—	0.0	—	0.0	—	ns
f _{MAX_IO}	Clock Frequency of I/O and PFU Register	ECP3-70EA/95EA	—	500	—	420	—	375	MHz
t _{CO}	Clock to Output - PIO Output Register	ECP3-35EA	—	3.7	_	4.1	—	4.5	ns
t _{SU}	Clock to Data Setup - PIO Input Register	ECP3-35EA	0.0	—	0.0	-	0.0	-	ns
t _H	Clock to Data Hold - PIO Input Register	ECP3-35EA	1.2	_	1.4	—	1.6	—	ns
t _{SU_DEL}	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-35EA	1.3	—	1.4	—	1.5	—	ns
t _{H_DEL}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-35EA	0.0	—	0.0	—	0.0	—	ns
f _{MAX_IO}	Clock Frequency of I/O and PFU Register	ECP3-35EA	—	500	—	420	—	375	MHz
t _{CO}	Clock to Output - PIO Output Register	ECP3-17EA	—	3.5	—	3.9	—	4.3	ns
t _{SU}	Clock to Data Setup - PIO Input Register	ECP3-17EA	0.0	—	0.0	—	0.0	—	ns
t _H	Clock to Data Hold - PIO Input Register	ECP3-17EA	1.3	_	1.5	—	1.6	—	ns
t _{SU_DEL}	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-17EA	1.3	—	1.4	—	1.5	—	ns
t _{H_DEL}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-17EA	0.0	—	0.0	—	0.0	—	ns
f _{MAX_IO}	Clock Frequency of I/O and PFU Register	ECP3-17EA	_	500	_	420	_	375	MHz
General I/O Pin Pa	rameters Using Dedicated Clock	nput Primary Clock w	ith PLL v	vith Cloc	k Injectio	on Remo	val Settir	וg²	
t _{COPLL}	Clock to Output - PIO Output Register	ECP3-150EA	_	3.3	_	3.6	—	39	ns
t _{SUPLL}	Clock to Data Setup - PIO Input Register	ECP3-150EA	0.7	—	0.8	—	0.9	—	ns
t _{HPLL}	Clock to Data Hold - PIO Input Register	ECP3-150EA	0.8	—	0.9	—	1.0	—	ns
t _{SU_DELPLL}	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-150EA	1.6	—	1.8	—	2.0	—	ns
^t H_DELPLL	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-150EA	—	0.0	—	0.0	—	0.0	ns
t _{COPLL}	Clock to Output - PIO Output Register	ECP3-70EA/95EA	_	3.3	_	3.5	_	3.8	ns
t _{SUPLL}	Clock to Data Setup - PIO Input Register	ECP3-70EA/95EA	0.7		0.8	_	0.9	_	ns

Over Recommended Commercial Operating Conditions



LatticeECP3 Internal Switching Characteristics^{1, 2, 5} (Continued)

		_	8	-7		-6		
Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Units.
t _{HWREN_EBR}	Hold Write/Read Enable to EBR Memory	0.141		0.145		0.149		ns
t _{SUCE_EBR}	Clock Enable Setup Time to EBR Output Register	0.087		0.096		0.104		ns
t _{HCE_EBR}	Clock Enable Hold Time to EBR Output Register	-0.066		-0.080		-0.094		ns
t _{SUBE_EBR}	Byte Enable Set-Up Time to EBR Output Register	-0.071		-0.070		-0.068		ns
t _{HBE_EBR}	Byte Enable Hold Time to EBR Output Register	0.118	_	0.098	_	0.077	_	ns
DSP Block Tin	ning ³							
t _{SUI_DSP}	Input Register Setup Time	0.32	_	0.36	_	0.39	_	ns
t _{HI_DSP}	Input Register Hold Time	-0.17	_	-0.19	_	-0.21	_	ns
t _{SUP_DSP}	Pipeline Register Setup Time	2.23	_	2.30	_	2.37	_	ns
t _{HP_DSP}	Pipeline Register Hold Time	-1.02	_	-1.09	_	-1.15	_	ns
t _{SUO_DSP}	Output Register Setup Time	3.09	_	3.22	_	3.34	_	ns
t _{HO_DSP}	Output Register Hold Time	-1.67	_	-1.76	_	-1.84	_	ns
t _{COI_DSP}	Input Register Clock to Output Time	_	3.05	_	3.35	_	3.73	ns
t _{COP_DSP}	Pipeline Register Clock to Output Time	_	1.30	_	1.47	_	1.64	ns
t _{COO_DSP}	Output Register Clock to Output Time	—	0.58	—	0.60	—	0.62	ns
t _{SUOPT_DSP}	Opcode Register Setup Time	0.31	_	0.35	_	0.39	_	ns
t _{HOPT_DSP}	Opcode Register Hold Time	-0.20	_	-0.24		-0.27	_	ns
t _{SUDATA_DSP}	Cascade_data through ALU to Output Register Setup Time	1.69		1.94		2.14		ns
t _{HPDATA_DSP}	Cascade_data through ALU to Output Register Hold Time	-0.58		-0.80		-0.97		ns

Over Recommended Commercial Operating Conditions

1. Internal parameters are characterized but not tested on every device.

2. Commercial timing numbers are shown. Industrial timing numbers are typically slower and can be extracted from the Diamond or ispLEVER software.

3. DSP slice is configured in Multiply Add/Sub 18 x 18 mode.

4. The output register is in Flip-flop mode.

5. For details on –9 speed grade devices, please contact your Lattice Sales Representative.



sysCLOCK PLL Timing

Parameter	Descriptions	Conditions	Clock	Min.	Тур.	Max.	Units
4	Input clock frequency (CLKI,		Edge clock	2		500	MHz
'IN	CLKFB)		Primary clock ⁴	2		420	MHz
4	Output clock frequency (CLKOP,		Edge clock	4		500	MHz
OUT	CLKOS)		Primary clock ⁴	4		420	MHz
f _{OUT1}	K-Divider output frequency	CLKOK		0.03125		250	MHz
f _{OUT2}	K2-Divider output frequency	CLKOK2		0.667		166	MHz
f _{VCO}	PLL VCO frequency			500		1000	MHz
f _{PFD} ³	Phase detector input frequency		Edge clock	2		500	MHz
			Primary clock ⁴	2		420	MHz
AC Charac	teristics						
t _{PA}	Programmable delay unit			65	130	260	ps
			Edge clock	45	50	55	%
t _{DT}	Output clock duty cycle	$f_{OUT} \le 250 \text{ MHz}$	Primary clock	45	50	55	%
		f _{OUT} > 250 MHz	Primary clock	30	50	70	%
t _{CPA}	Coarse phase shift error (CLKOS, at all settings)			-5	0	+5	% of period
t _{OPW}	Output clock pulse width high or low (CLKOS)			1.8	_	_	ns
		$f_{OUT} \ge 420 \text{ MHz}$			_	200	ps
t _{OPJIT} 1	Output clock period jitter	420 MHz > f _{OUT} ≥ 100 MHz		—		250	ps
		f _{OUT} < 100 MHz		—	—	0.025	UIPP
t _{SK}	Input clock to output clock skew when N/M = integer			—		500	ps
. 2		2 to 25 MHz			_	200	us
LOCK_		25 to 500 MHz		—	—	50	us
t _{UNLOCK}	Reset to PLL unlock time to ensure fast reset			_		50	ns
t _{HI}	Input clock high time	90% to 90%		0.5		_	ns
t _{LO}	Input clock low time	10% to 10%		0.5	_	_	ns
t _{IPJIT}	Input clock period jitter			_	—	400	ps
	Reset signal pulse width high, RSTK			10		_	ns
^I RST	Reset signal pulse width high, RST			500	_	_	ns

Over Recommended Operating Conditions

1. Jitter sample is taken over 10,000 samples of the primary PLL output with clean reference clock with no additional I/O toggling.

2. Output clock is valid after t_{LOCK} for PLL reset and dynamic delay adjustment.

3. Period jitter and cycle-to-cycle jitter numbers are guaranteed for $f_{PFD} > 4$ MHz. For $f_{PFD} < 4$ MHz, the jitter numbers may not be met in certain conditions. Please contact the factory for $f_{PFD} < 4$ MHz.

4. When using internal feedback, maximum can be up to 500 MHz.



Table 3-7. Channel Output Jitter

Description	Frequency	Min.	Тур.	Max.	Units
Deterministic	3.125 Gbps	—	—	0.17	UI, p-p
Random	3.125 Gbps	—	—	0.25	UI, p-p
Total	3.125 Gbps	—	—	0.35	UI, p-p
Deterministic	2.5 Gbps	—	—	0.17	UI, p-p
Random	2.5 Gbps	—	—	0.20	UI, p-p
Total	2.5 Gbps	—	—	0.35	UI, p-p
Deterministic	1.25 Gbps	—	—	0.10	UI, p-p
Random	1.25 Gbps	—	—	0.22	UI, p-p
Total	1.25 Gbps	—	—	0.24	UI, p-p
Deterministic	622 Mbps	—	—	0.10	UI, p-p
Random	622 Mbps	—	—	0.20	UI, p-p
Total	622 Mbps	—	—	0.24	UI, p-p
Deterministic	250 Mbps	—	—	0.10	UI, p-p
Random	250 Mbps	—	—	0.18	UI, p-p
Total	250 Mbps	—	—	0.24	UI, p-p
Deterministic	150 Mbps	—	—	0.10	UI, p-p
Random	150 Mbps	—	—	0.18	UI, p-p
Total	150 Mbps	—		0.24	UI, p-p

Note: Values are measured with PRBS 2⁷-1, all channels operating, FPGA logic active, I/Os around SERDES pins quiet, reference clock @ 10X mode.



SERDES External Reference Clock

The external reference clock selection and its interface are a critical part of system applications for this product. Table 3-12 specifies reference clock requirements, over the full range of operating conditions.

Symbol	Description	Min.	Тур.	Max.	Units
F _{REF}	Frequency range	15	_	320	MHz
F _{REF-PPM}	Frequency tolerance ¹	-1000	_	1000	ppm
V _{REF-IN-SE}	Input swing, single-ended clock ²	200	_	V _{CCA}	mV, p-p
V _{REF-IN-DIFF}	Input swing, differential clock	200	_	2*V _{CCA}	mV, p-p differential
V _{REF-IN}	Input levels	0	_	V _{CCA} + 0.3	V
D _{REF}	Duty cycle ³	40	_	60	%
T _{REF-R}	Rise time (20% to 80%)	200	500	1000	ps
T _{REF-F}	Fall time (80% to 20%)	200	500	1000	ps
Z _{REF-IN-TERM-DIFF}	Differential input termination	-20%	100/2K	+20%	Ohms
C _{REF-IN-CAP}	Input capacitance	_	—	7	pF

Table 3-12. External Reference Clock Specification (refclkp/refclkn)

1. Depending on the application, the PLL_LOL_SET and CDR_LOL_SET control registers may be adjusted for other tolerance values as described in TN1176, LatticeECP3 SERDES/PCS Usage Guide.

2. The signal swing for a single-ended input clock must be as large as the p-p differential swing of a differential input clock to get the same gain at the input receiver. Lower swings for the clock may be possible, but will tend to increase jitter.

3. Measured at 50% amplitude.

Figure 3-13. SERDES External Reference Clock Waveforms





XAUI/Serial Rapid I/O Type 3/CPRI LV E.30 Electrical and Timing Characteristics

AC and DC Characteristics

Table 3-13. Transmit

Over Recommended Operating Conditions

Symbol	Description	Test Conditions	Min.	Тур.	Max.	Units
T _{RF}	Differential rise/fall time	20%-80%	_	80	—	ps
Z _{TX_DIFF_DC}	Differential impedance		80	100	120	Ohms
J _{TX_DDJ} ^{2, 3, 4}	Output data deterministic jitter		_	—	0.17	UI
J _{TX_TJ} ^{1, 2, 3, 4}	Total output data jitter		_	—	0.35	UI

1. Total jitter includes both deterministic jitter and random jitter.

2. Jitter values are measured with each CML output AC coupled into a 50-Ohm impedance (100-Ohm differential impedance).

3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.

4. Values are measured at 2.5 Gbps.

Table 3-14. Receive and Jitter Tolerance

Over Recommended Operating Conditions

Symbol	Description Test Conditions		Min.	Тур.	Max.	Units
RL _{RX_DIFF}	Differential return loss	From 100 MHz to 3.125 GHz	10	_	_	dB
RL _{RX_CM}	Common mode return loss	From 100 MHz to 3.125 GHz		_	_	dB
Z _{RX_DIFF}	Differential termination resistance		80	100	120	Ohms
J _{RX_DJ} ^{1, 2, 3}	Deterministic jitter tolerance (peak-to-peak)		—	_	0.37	UI
J _{RX_RJ} ^{1, 2, 3}	Random jitter tolerance (peak-to-peak)		—	_	0.18	UI
J _{RX_SJ} ^{1, 2, 3}	Sinusoidal jitter tolerance (peak-to-peak)		—	_	0.10	UI
J _{RX_TJ} ^{1, 2, 3}	Total jitter tolerance (peak-to-peak)		—	_	0.65	UI
T _{RX_EYE}	Receiver eye opening		0.35		_	UI

1. Total jitter includes deterministic jitter, random jitter and sinusoidal jitter. The sinusoidal jitter tolerance mask is shown in Figure 3-18.

2. Jitter values are measured with each high-speed input AC coupled into a 50-Ohm impedance.

3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.

4. Jitter tolerance parameters are characterized when Full Rx Equalization is enabled.

5. Values are measured at 2.5 Gbps.



SMPTE SD/HD-SDI/3G-SDI (Serial Digital Interface) Electrical and Timing Characteristics

AC and DC Characteristics

Table 3-19. Transmit

Symbol	Description Test Conditions Min.			Тур.	Max.	Units
BR _{SDO}	Serial data rate		270	—	2975	Mbps
T _{JALIGNMENT} ²	Serial output jitter, alignment	270 Mbps	—	—	0.20	UI
T _{JALIGNMENT} ²	Serial output jitter, alignment	1485 Mbps		—	0.20	UI
T _{JALIGNMENT} ^{1, 2}	Serial output jitter, alignment	2970Mbps	—	—	0.30	UI
T _{JTIMING}	Serial output jitter, timing	270 Mbps	—	—	0.20	UI
T _{JTIMING}	Serial output jitter, timing	1485 Mbps	—	—	1.0	UI
T _{JTIMING}	Serial output jitter, timing	2970 Mbps	—	_	2.0	UI

Notes:

 Timing jitter is measured in accordance with SMPTE RP 184-1996, SMPTE RP 192-1996 and the applicable serial data transmission standard, SMPTE 259M-1997 or SMPTE 292M (proposed). A color bar test pattern is used. The value of f_{SCLK} is 270 MHz or 360 MHz for SMPTE 259M, 540 MHz for SMPTE 344M or 1485 MHz for SMPTE 292M serial data rates. See the Timing Jitter Bandpass section.

2. Jitter is defined in accordance with SMPTE RP1 184-1996 as: jitter at an equipment output in the absence of input jitter.

3. All Tx jitter is measured at the output of an industry standard cable driver; connection to the cable driver is via a 50 Ohm impedance differential signal from the Lattice SERDES device.

4. The cable driver drives: RL=75 Ohm, AC-coupled at 270, 1485, or 2970 Mbps, RREFLVL=RREFPRE=4.75 kOhm 1%.

Table 3-20. Receive

Symbol	Description	Test Conditions	Min.	Тур.	Max.	Units
BR _{SDI}	Serial input data rate		270	_	2970	Mbps
CID	Stream of non-transitions (=Consecutive Identical Digits)		7(3G)/26(SMPTE Triple rates) @ 10-12 BER	_	_	Bits

Table 3-21. Reference Clock

Symbol	Description	Test Conditions	Min.	Тур.	Max.	Units
F _{VCLK}	Video output clock frequency		27	-	74.25	MHz
DCV	Duty cycle, video clock		45	50	55	%



Figure 3-19. Test Loads

Test Loads









LatticeECP3 sysCONFIG Port Timing Specifications

Parameter	r Description			Max.	Units
POR, Confi	guration Initialization, and Wakeup				1
	Time from the Application of V_{CC} , V_{CCAUX} or V_{CCIO8}^{*} (Whichever	Master mode		23	ms
t _{ICFG}	is the Last to Cross the POR Trip Point) to the Rising Edge of INITN	Slave mode	—	6	ms
t _{VMC}	Time from t _{ICFG} to the Valid Master MCLK		—	5	μs
t _{PRGM}	PROGRAMN Low Time to Start Configuration		25	—	ns
t _{PRGMRJ}	PROGRAMN Pin Pulse Rejection		_	10	ns
t _{DPPINIT}	Delay Time from PROGRAMN Low to INITN Low		—	37	ns
t _{DPPDONE}	Delay Time from PROGRAMN Low to DONE Low		_	37	ns
t _{DINIT} 1	PROGRAMN High to INITN High Delay		—	1	ms
t _{MWC}	Additional Wake Master Clock Signals After DONE Pin is High		100	500	cycles
t _{CZ}	MCLK From Active To Low To High-Z		—	300	ns
t _{IODISS}	User I/O Disable from PROGRAMN Low			100	ns
t _{IOENSS}	User I/O Enabled Time from CCLK Edge During Wake-up Sequer	ice		100	ns
All Configu	ration Modes				
t _{SUCDI}	Data Setup Time to CCLK/MCLK		5	—	ns
t _{HCDI}	Data Hold Time to CCLK/MCLK		1	—	ns
t _{CODO}	CCLK/MCLK to DOUT in Flowthrough Mode		-0.2	12	ns
Slave Seria	l				1
t _{SSCH}	CCLK Minimum High Pulse	5	—	ns	
t _{SSCL}	CCLK Minimum Low Pulse	5	_	ns	
	Without encryption		_	33	MHz
ICCLK	CCLK Frequency	With encryption		20	MHz
Master and	Slave Parallel	1			
t _{SUCS}	CSN[1:0] Setup Time to CCLK/MCLK		7	—	ns
t _{HCS}	CSN[1:0] Hold Time to CCLK/MCLK		1	—	ns
t _{SUWD}	WRITEN Setup Time to CCLK/MCLK		7	_	ns
t _{HWD}	WRITEN Hold Time to CCLK/MCLK		1	_	ns
t _{DCB}	CCLK/MCLK to BUSY Delay Time		_	12	ns
t _{CORD}	CCLK to Out for Read Data		_	12	ns
t _{BSCH}	CCLK Minimum High Pulse		6	_	ns
t _{BSCL}	CCLK Minimum Low Pulse		6	—	ns
t _{BSCYC}	Byte Slave Cycle Time		30	_	ns
		Without encryption	_	33	MHz
ICCLK	CCLK CCLK/MCLK Frequency With enc		—	20	MHz
Master and	Slave SPI	1			
t _{CFGX}	INITN High to MCLK Low			80	ns
t _{CSSPI}	INITN High to CSSPIN Low			2	μs
t _{SOCDO}	MCLK Low to Output Valid			15	ns
t _{CSPID}	CSSPIN[0:1] Low to First MCLK Edge Setup Time				μs
	001// 5	Without encryption	—	33	MHz
ICCLK	CCLK Frequency	With encryption	—	20	MHz
t _{SSCH}	CCLK Minimum High Pulse		5		ns

Over Recommended Operating Conditions



Figure 3-30. SPI Configuration Waveforms



Figure 3-31. Slave SPI HOLDN Waveforms





sysl/O Differential Electrical Characteristics

Transition Reduced LVDS (TRLVDS DC Specification)

Over Recommended Operating Conditions

Symbol	Description	Min.	Nom.	Max.	Units
V _{CCO}	Driver supply voltage (+/- 5%)	3.14	3.3	3.47	V
V _{ID}	Input differential voltage	150	_	1200	mV
V _{ICM}	Input common mode voltage	3	_	3.265	V
V _{CCO}	Termination supply voltage	3.14	3.3	3.47	V
R _T	Termination resistance (off-chip)	45	50	55	Ohms

Note: LatticeECP3 only supports the TRLVDS receiver.



Mini LVDS

Over Recommended Operating Conditions

Parameter Symbol	Description	Min.	Тур.	Max.	Units
Z _O	Single-ended PCB trace impedance	30	50	75	Ohms
R _T	Differential termination resistance	50	100	150	Ohms
V _{OD}	Output voltage, differential, V _{OP} - V _{OM}	300	_	600	mV
V _{OS}	Output voltage, common mode, $ V_{OP} + V_{OM} /2$	1	1.2	1.4	V
ΔV_{OD}	Change in V _{OD} , between H and L	—	_	50	mV
ΔV_{ID}	Change in V_{OS} , between H and L	—	_	50	mV
V _{THD}	Input voltage, differential, V _{INP} - V _{INM}	200	_	600	mV
V _{CM}	Input voltage, common mode, $ V_{INP} + V_{INM} /2$	0.3+(V _{THD} /2)	_	2.1-(V _{THD} /2)	
T _R , T _F	Output rise and fall times, 20% to 80%	—	_	550	ps
T _{ODUTY}	Output clock duty cycle	40	—	60	%

Note: Data is for 6 mA differential current drive. Other differential driver current options are available.



Date	Version	Section	Change Summary
			Updated Simplified Channel Block Diagram for SERDES/PCS Block diagram.
			Updated Device Configuration text section.
			Corrected software default value of MCCLK to be 2.5 MHz.
		DC and Switching Characteristics	Updated VCCOB Min/Max data in Recommended Operating Conditions table.
			Corrected footnote 2 in sysIO Recommended Operating Conditions table.
			Added added footnote 7 for t _{SKEW_PRIB} to External Switching Characteristics table.
			Added 2-to-1 Gearing text section and table.
			Updated External Reference Clock Specification (refclkp/refclkn) table.
			LatticeECP3 sysCONFIG Port Timing Specifications - updated t _{DINIT} information.
			Added sysCONFIG Port Timing waveform.
			Serial Input Data Specifications table, delete Typ data for $V_{RX-DIFF-S}$.
			Added footnote 4 to sysCLOCK PLL Timing table for t _{PFD} .
			Added SERDES/PCS Block Latency Breakdown table.
			External Reference Clock Specifications table, added footnote 4, add symbol name vREF-IN-DIFF.
			Added SERDES External Reference Clock Waveforms.
			Updated Serial Output Timing and Levels table.
			Pin-to-pin performance table, changed "typically 3% slower" to "typically slower".
			Updated timing information
			Updated SERDES minimum frequency.
			Added data to the following tables: External Switching Characteristics, Internal Switching Characteristics, Family Timing Adders, Maximum I/O Buffer Speed, DLL Timing, High Speed Data Transmitter, Channel Out- put Jitter, Typical Building Block Function Performance, Register-to- Register Performance, and Power Supply Requirements.
			Updated Serial Input Data Specifications table.
			Updated Transmit table, Serial Rapid I/O Type 2 Electrical and Timing Characteristics section.
		Pinout Information	Updated Signal Description tables.
			Updated Pin Information Summary tables and added footnote 1.
February 2009	01.0	_	Initial release.